

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-10. (Canceled).

11. (Currently Amended) A magnetic memory cell comprising a switching element and a magnetic tunnel junction (MTJ) configuration comprising:

a first MTJ device including a first free layer, a first tunneling barrier, and a first pinned layer;

a second MTJ device including a second free layer, a second tunneling barrier, and a second pinned layer, wherein the second tunneling barrier is comprised of a different material than the first tunneling barrier; and

a first conductor connecting the first and second MTJ devices;

wherein a first magneto-resistance of the first MTJ device is different in magnitude relative to a second magneto-resistance of the second MTJ device.

12. (Original) The memory cell of claim 11 wherein the second magneto-resistance is twice of the first magnetic resistance.

13. (Original) The memory cell of claim 11 wherein the second MTJ device includes an anti-ferromagnetic material and wherein the first free layer is connected to the anti-ferromagnetic material through the first conductor.

14. (Original) The memory cell of claim 11 wherein the MTJ configuration further comprises:

a second conductor connected to the second free layer;  
wherein the first conductor connects to the first free layer and  
wherein the first and second MTJ devices can be simultaneously written to using the second and first conductors respectively.

15. (Original) The memory cell of claim 11 wherein at least one of the free layers includes a spacer sandwiched between two ferromagnetic layers.

16. (Canceled).

17. (Original) The memory cell of claim 11 wherein the first tunneling barrier is formed from a different processing recipe than the second tunneling layer.

18. (Currently Amended) An integrated circuit comprising:  
an input/output section;  
a plurality of logic circuits connected to the input/output section; and  
a plurality of magnetic memory cells connected to the logic circuits, the magnetic memory cells including a transistor and a storage structure including:  
a first magnetic junction device including a first free layer, a first tunneling barrier, and a first pinned layer;  
a second magnetic junction device including a second free layer, a second tunneling barrier, and a second pinned layer, wherein the second tunneling barrier is comprised of a different material than the first tunneling barrier; and  
a first conductor connected to configure the first and second magnetic junction devices in parallel;  
wherein a first magneto-resistance ratio of the first magnetic junction device is different in magnitude relative to a second magneto-resistance ratio of the second magnetic junction device.

19. (Canceled).

20. (Original) The integrated circuit of claim 18 wherein the second magnetic junction device includes an anti-ferromagnetic material and wherein the first free layer is connected to the anti-ferromagnetic material through the first conductor.

21. (Original) The integrated circuit of claim 18 further comprising;  
a second conductor connected to the second free layer;  
wherein the first conductor connects to the first free layer; and  
wherein the first and second magnetic junction devices can be simultaneously written to using the second and first conductors respectively.

22. (Original) The integrated circuit of claim 18 wherein at least one of the free layers includes a spacer sandwiched between two ferromagnetic layers.

23. (Original) The integrated circuit of claim 22 wherein the spacer comprises a synthetic anti-ferromagnetic material.

24. (Canceled).

25. (Original) The integrated circuit of claim 18 wherein the first tunneling barrier is formed from a different processing recipe than the second tunneling barrier.

26. (Previously Presented) The integrated circuit of claim 18 wherein the first magneto-resistance ratio of the first tunneling barrier is 50-60% and the second magneto-resistance ratio of the second tunneling barrier is 20-30%.

27. (Currently Amended) An apparatus, comprising:  
a first magnetic tunnel junction having a first magneto-resistance ratio of 50-60%; and  
a second magnetic tunnel junction having a second magneto-resistance ratio of 20-30%,  
wherein:

the first and second magnetic tunnel junctions are electrically connected; ~~and~~  
~~the first magneto-resistance ratio and the second magneto-resistance ratio are~~  
~~substantially different, at least with respect to magnitude.~~

28. (Previously Presented) The apparatus of claim 27 wherein the first magneto-resistance ratio is about 50% of the second magneto-resistance ratio.

29. (Previously Presented) The apparatus of claim 27 wherein:  
the first magnetic tunnel junction has a first tunnel barrier having a first composition;  
the second magnetic tunnel junction has a second tunnel barrier having a second composition; and  
the first and second compositions are different.

30. (Previously Presented) The apparatus of claim 27 wherein a first magnetic layer of the first magnetic tunnel junction is located between the second magnetic tunnel junction and a second magnetic layer of the first magnetic tunnel junction.

31. (Previously Presented) The apparatus of claim 27 wherein no magnetic layer of the first magnetic tunnel junction is located between the second magnetic tunnel junction and any other magnetic layer of the first magnetic tunnel junction.

32. (Previously Presented) The apparatus of claim 27 wherein:  
the first magnetic tunnel junction comprises a pinned layer, a first free layer, and a first tunnel barrier located between the pinned layer and the first free layer; and  
the second magnetic tunnel junction comprises the first free layer, a second free layer, and a second tunnel barrier located between the first and second free layers.